



# Quantum Confinement in Security Elements



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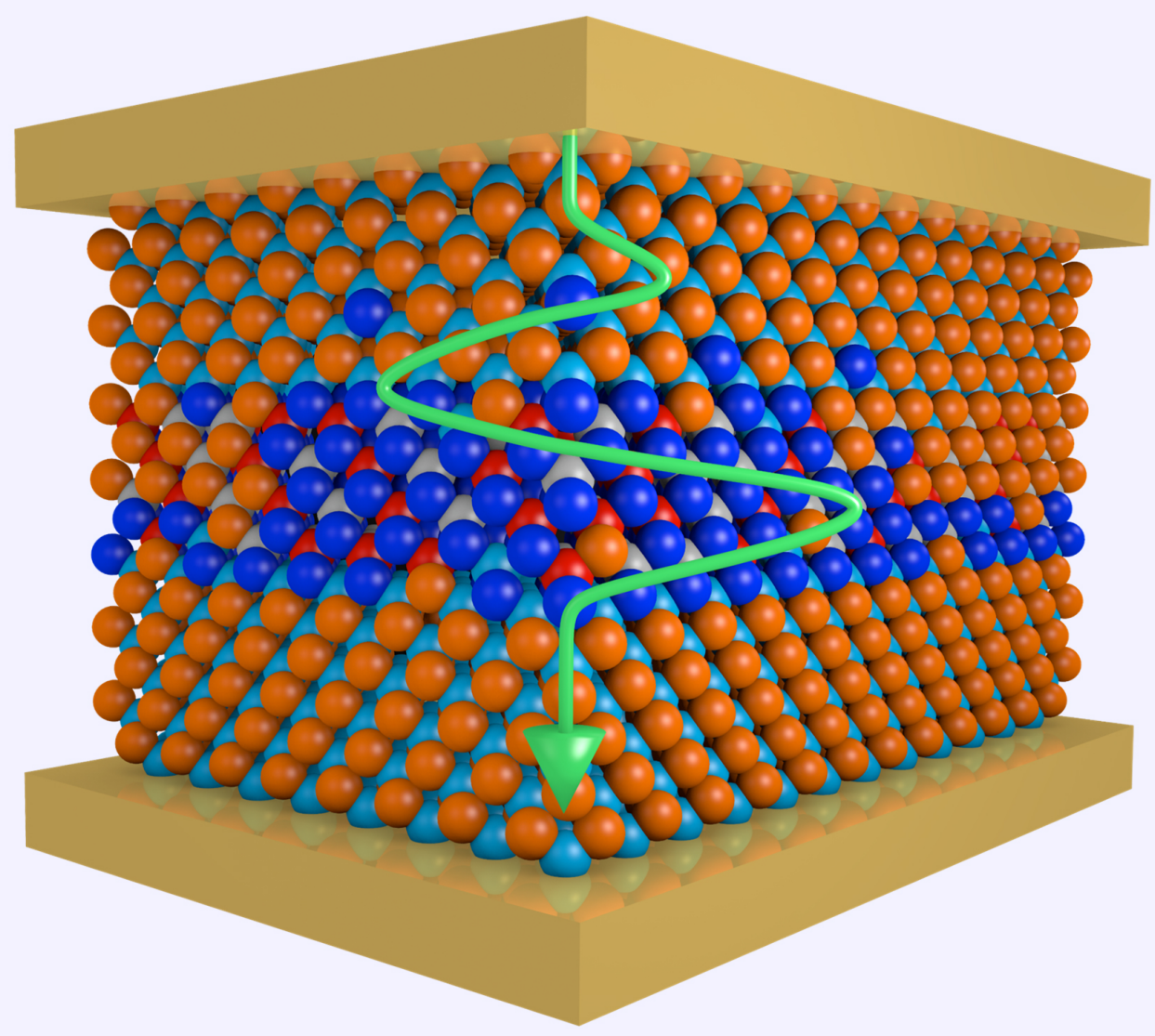
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Quantum Base

## 1) Introduction to Quantum Confinement and Resonant Tunnelling Diodes

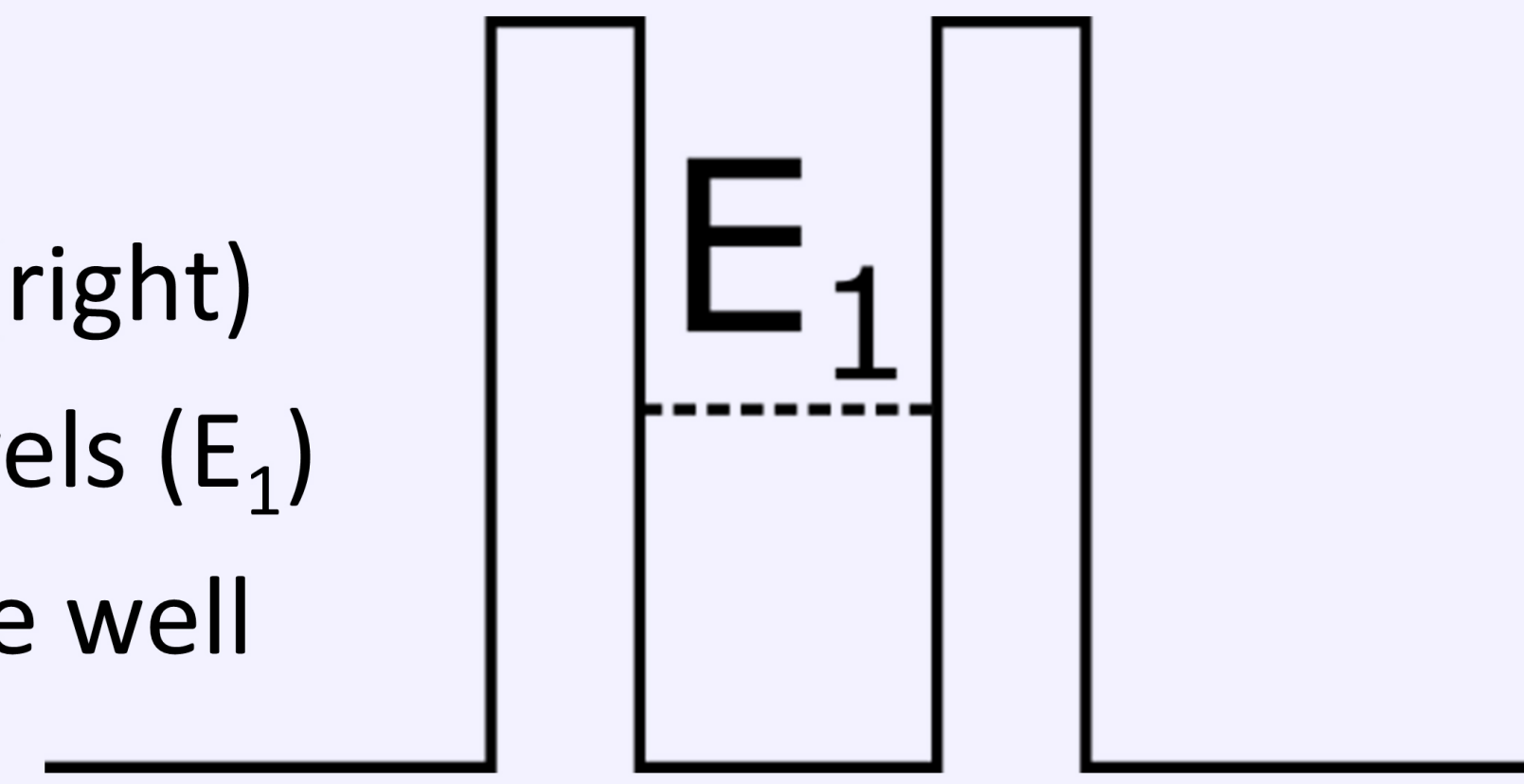
**Quantum confinement** occurs when a particle such as an electron is confined on the length scale of its wavelength.

When an electron is strongly quantum confined, it can only exist at discrete energy levels.



### Resonant Tunnelling Diodes (RTDs):

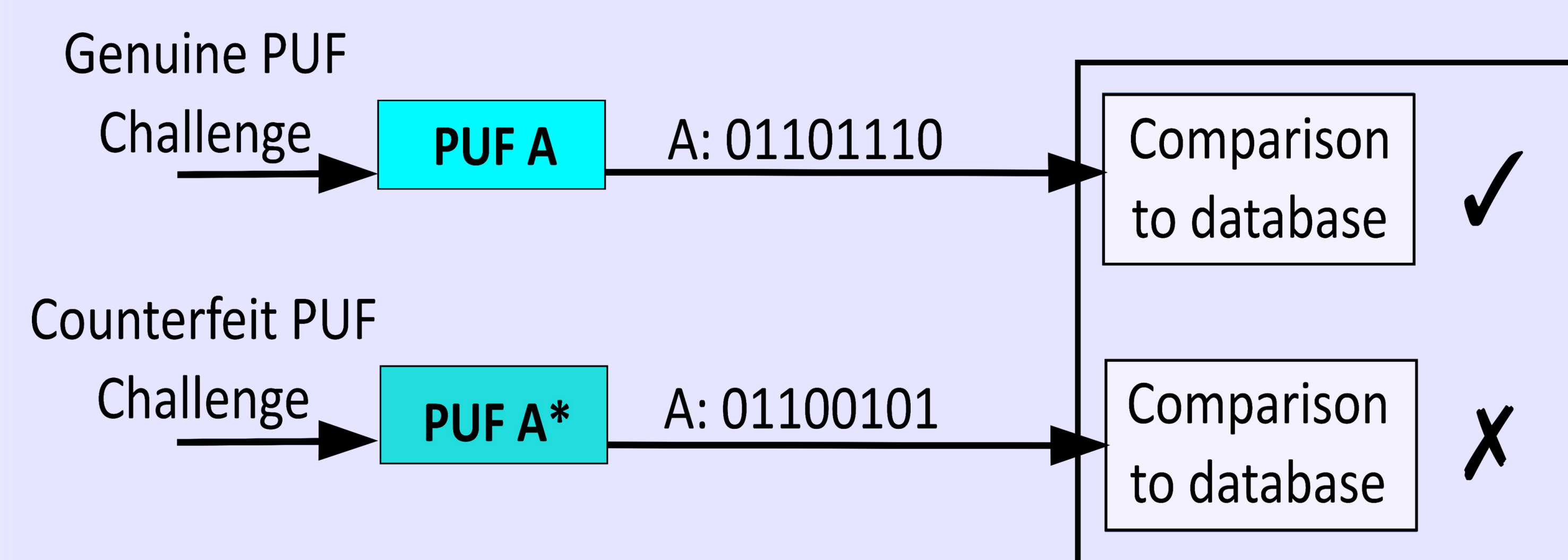
- One of the simplest quantum confinement structures
- Consists of a matrix of atoms (left), defining a quantum well (right)
- Central region is sufficiently small to form discrete energy levels ( $E_1$ )
- Energy level is very sensitive to the atomic constituents of the well



## 2) RTDs as Physically Unclonable Functions

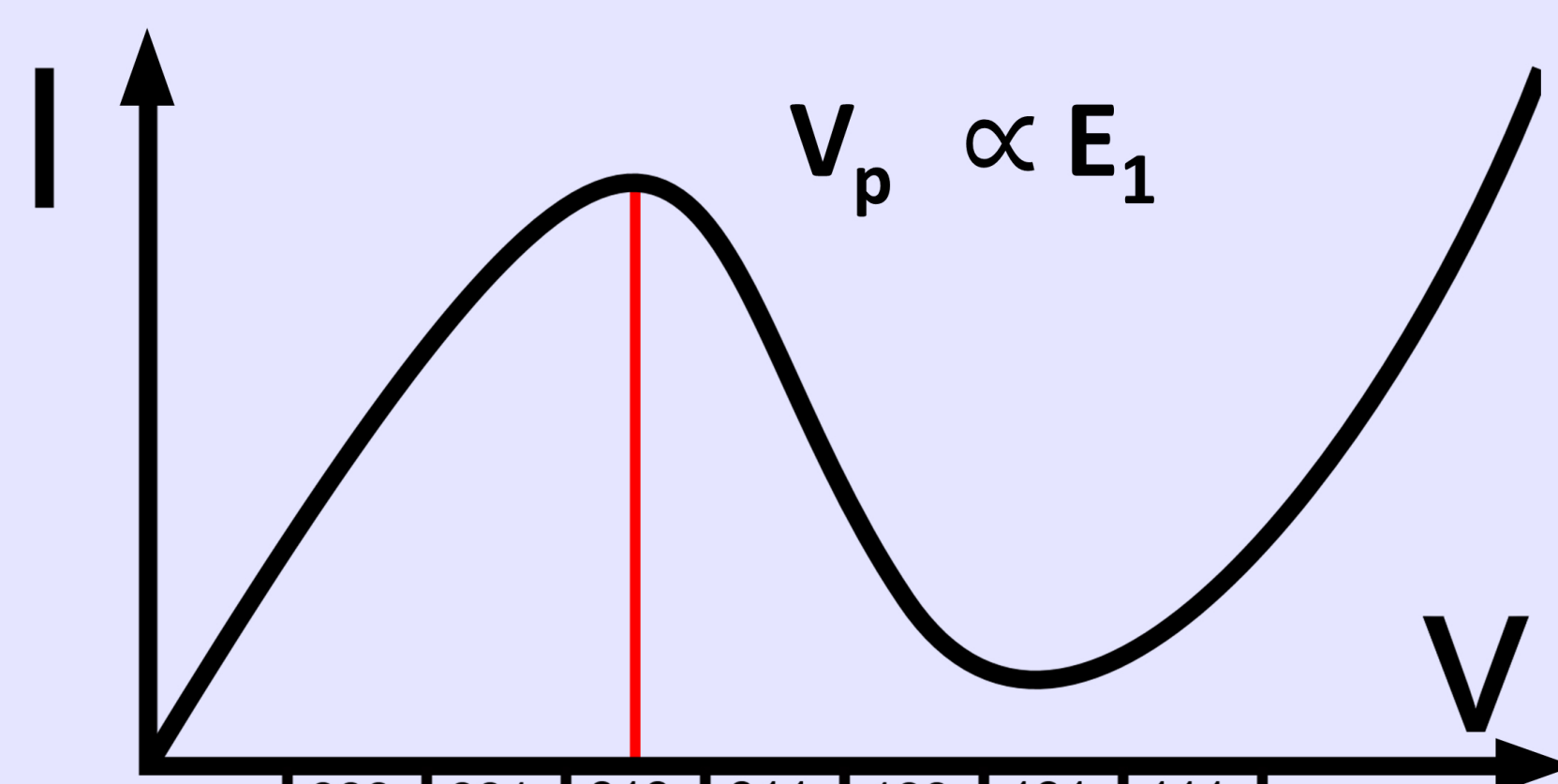
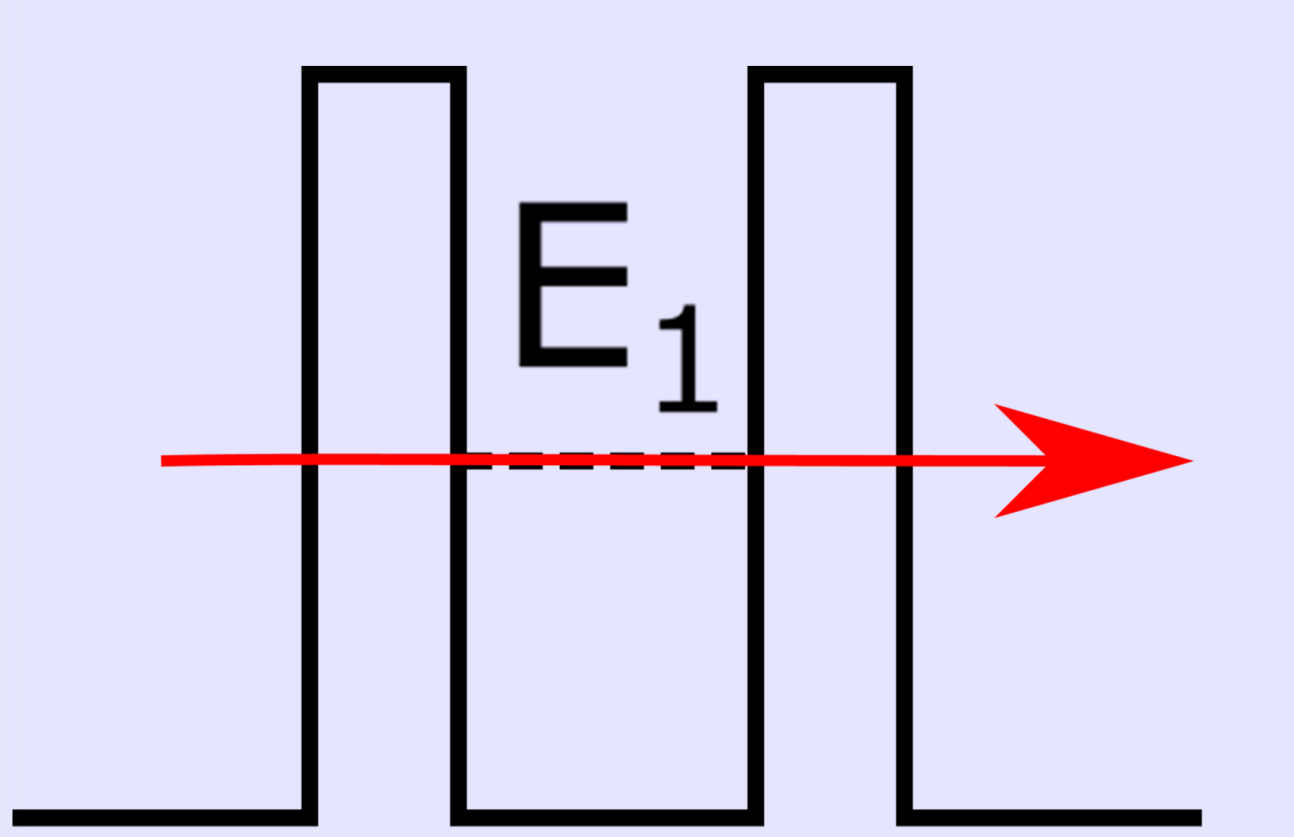
Physically Unclonable Functions (PUFs):

- Unique physical objects that cannot be recreated
- Translates an applied challenge to a unique response
- Can act as 'fingerprint' for attached circuitry or objects



If **voltage** is controlled over RTD, we have a PUF:

- At voltage of peak ( $V_p$ ), the most electrons have energy  $E_1$ 
  - $V_p$  position directly depends on energy level position  $E_1$
  - $E_1$  depends on **precise atomic arrangement** in the well
- **Replication** requires characterising and fabricating the device at **atomic-level resolution** (impossible)



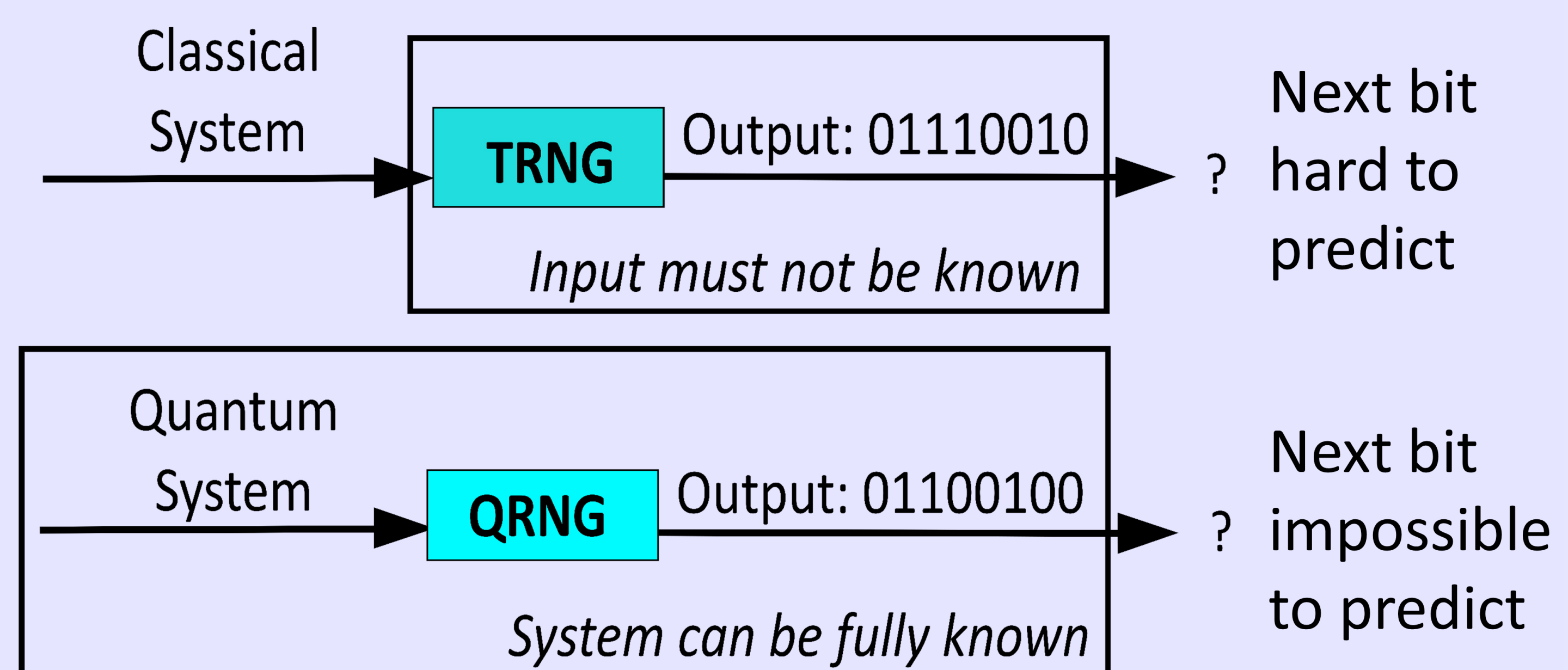
Band structure of RTD PUF

IV characteristic of RTD PUF

## 3) RTDs for Quantum Random Numbers

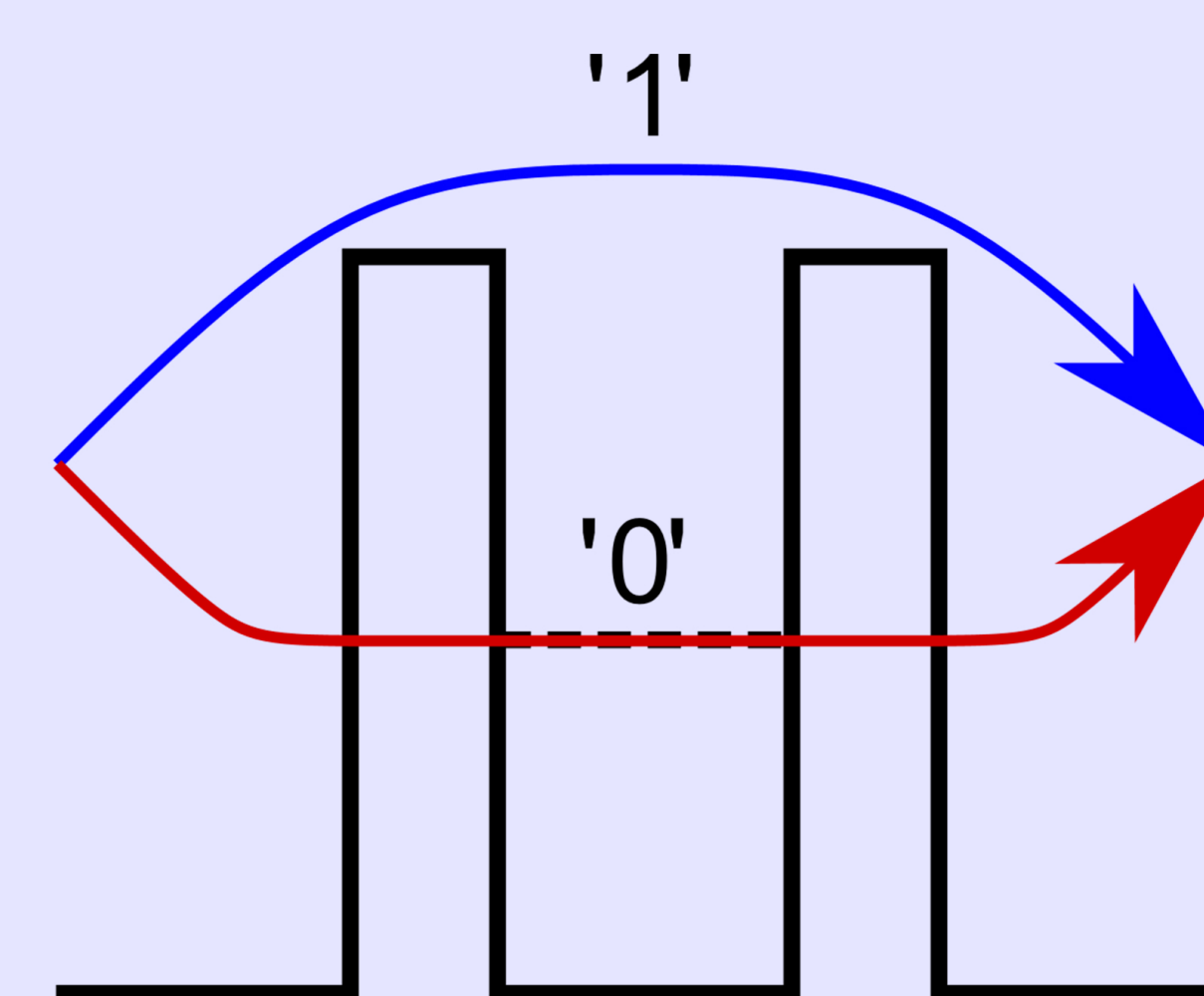
Quantum Random Number Generators (QRNGs):

- Unpredictable random number generator
- Uses quantum processes that are entirely indeterminable
- Cannot predict output, even with knowing entire system

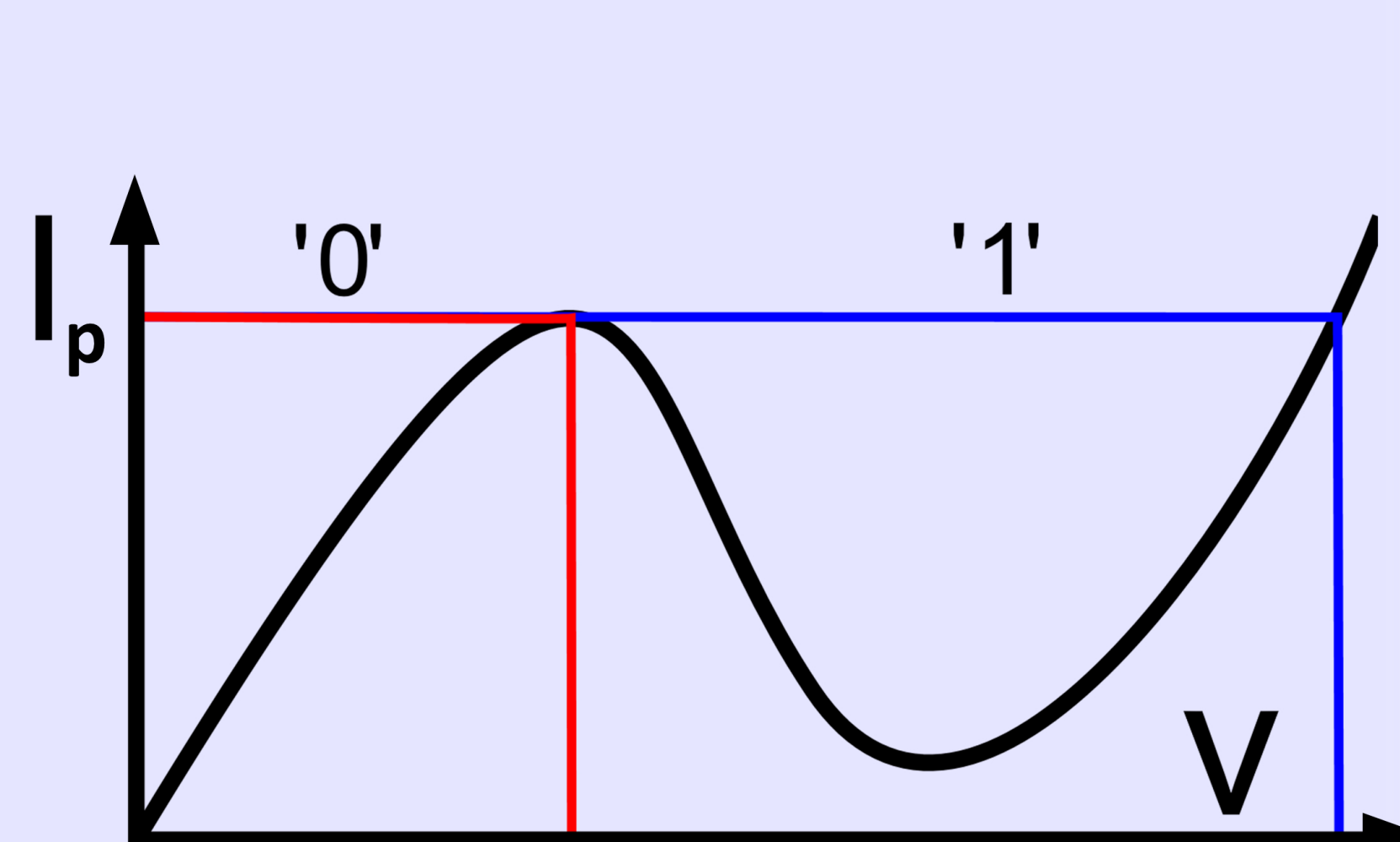


If **current** is controlled over the RTD, we have a QRNG:

- At peak current  $I_p$ , incident **electron can pass 1 of 2 ways**:
  - **50% chance** of **tunnelling through** the barriers
  - **50% chance** of **jumping over** the barriers
- The path the electron takes is **quantum non-deterministic**, and so cannot be predicted, but can be **easily measured**



Band structure of RTD RNG



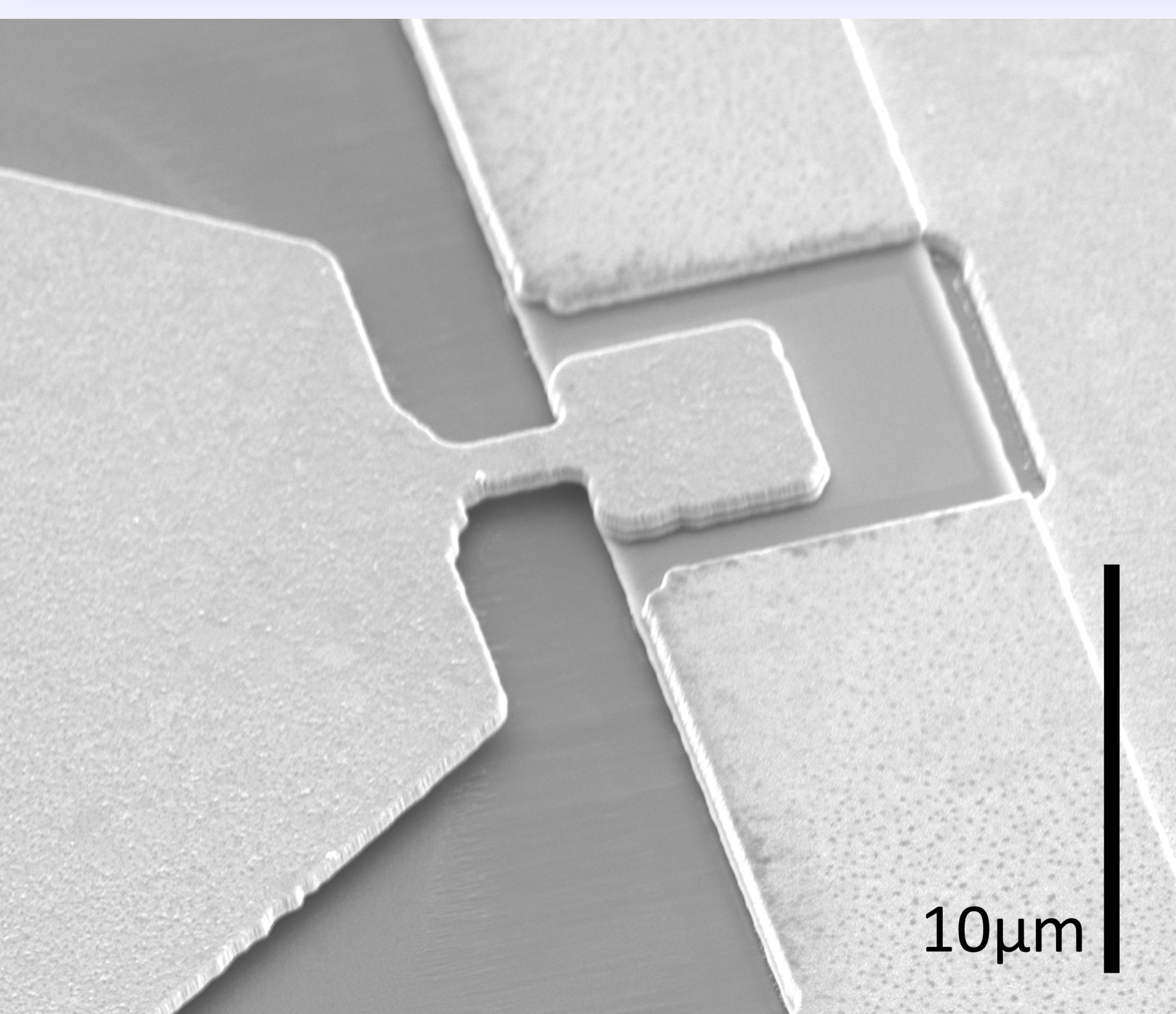
IV characteristic of RTD RNG

## 4) RTDs in CMOS

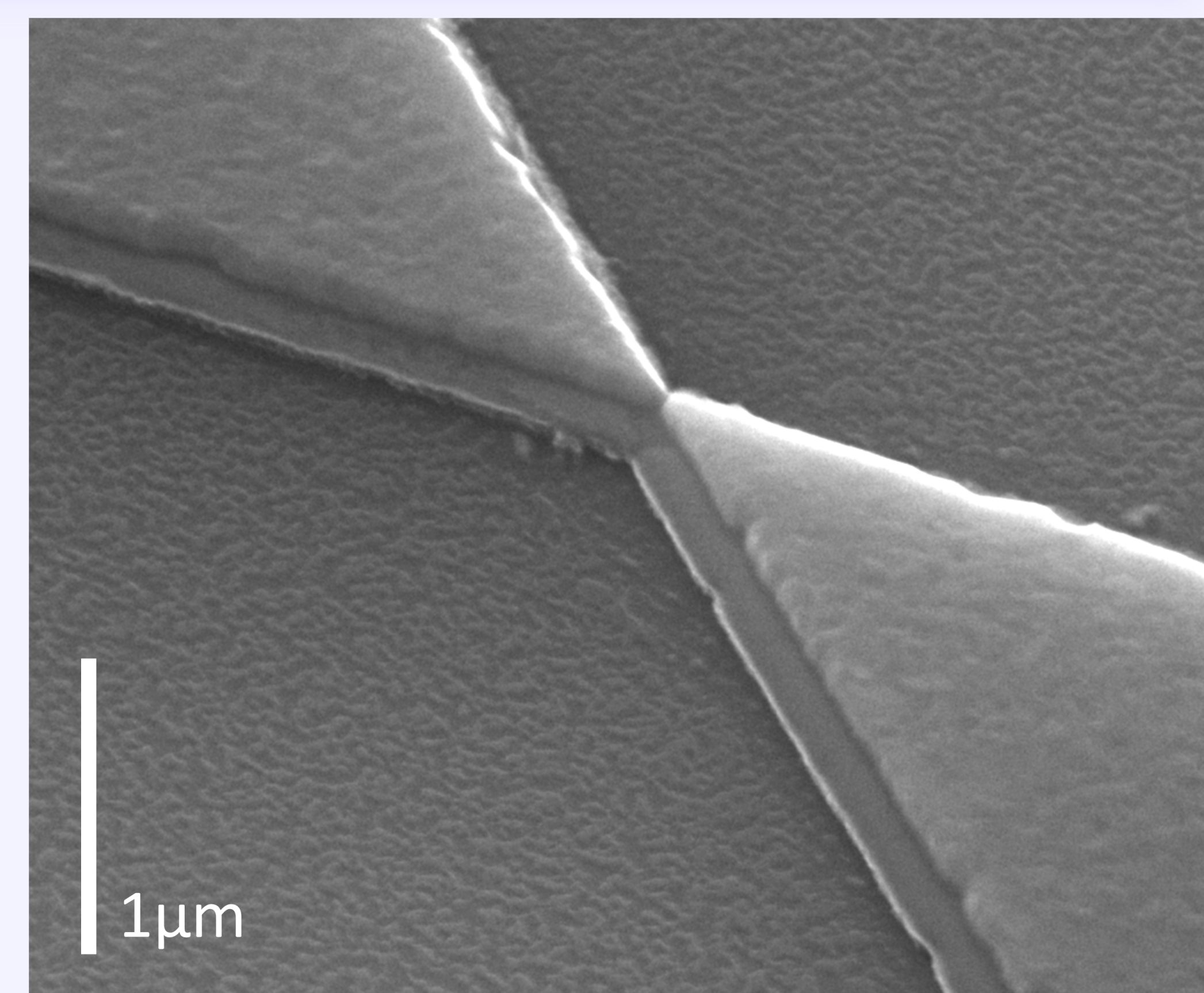
Typical resonant tunnelling diodes use III/V semiconductor material (Left – InGaAs/AlAs)

This material can't be directly integrated into CMOS circuit fabrication processes

Work is being done to produce RTDs in CMOS-compatible silicon (Right – Si/SiO<sub>2</sub>)



10μm



1μm